

HL6548FG

Visible High Power Laser Diode

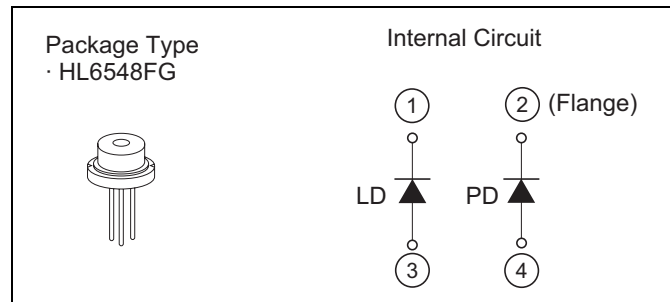
ODE-208-015C (Z)
Rev.3
Mar. 13, 2006

Description

The HL6548FG is a 0.65 μm band AlGaInP laser diode (LD) with a multi-quantum well (MQW) structure. It is suitable as a light source for measurement, and various other types of optical equipment.

Features

- Optical output power : 90mW CW operation
- Single longitudinal mode.
- Visible light output : $\lambda_p = 660 \text{ nm Typ}$



Note: This type is preliminary. Therefore, this data sheet may be changed without any notice.

4pin package (FG type) : Isolated LD polarity from flange (stem)

Absolute Maximum Ratings

($T_C = 25^\circ\text{C}$)

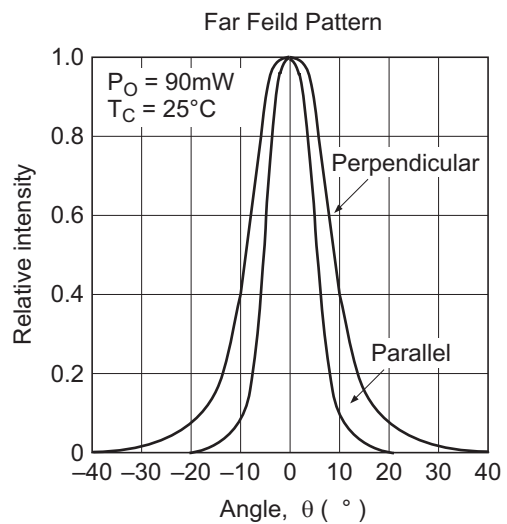
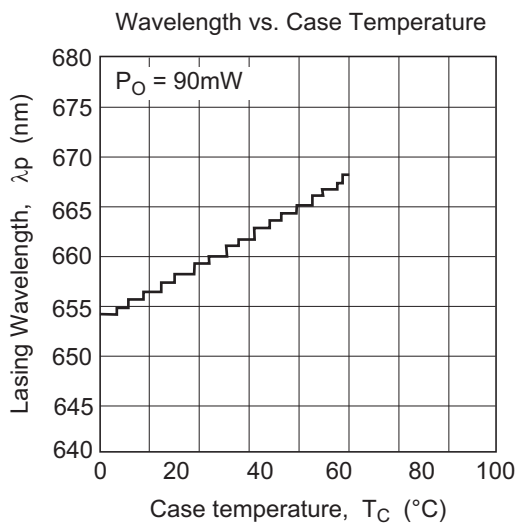
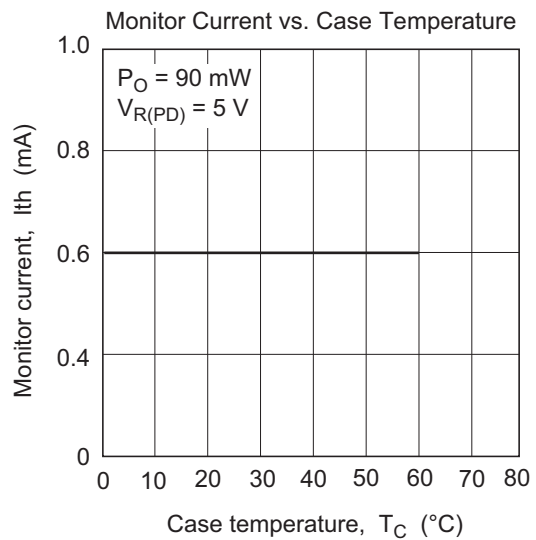
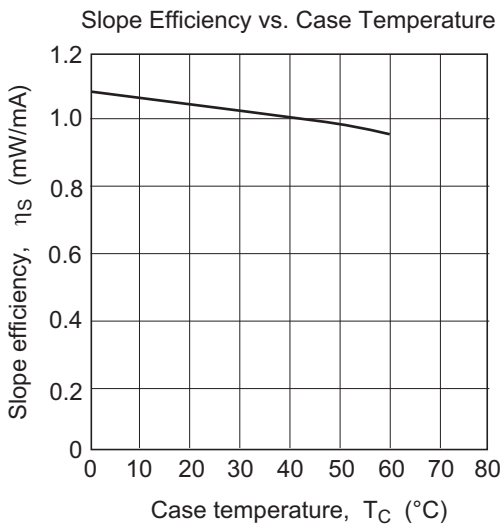
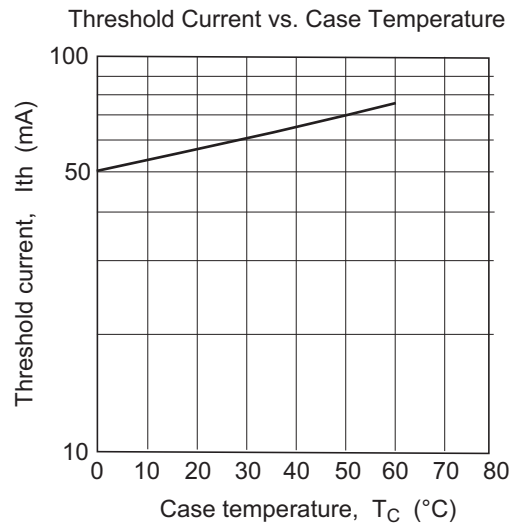
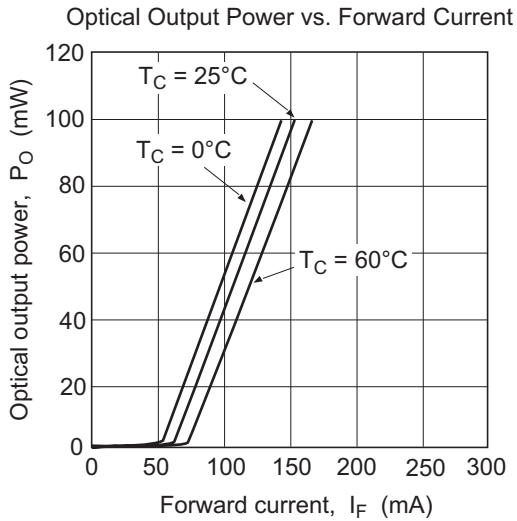
Item	Symbol	Ratings	Unit
Optical output power	P_O	100	mW
LD reverse voltage	$V_{R(LD)}$	2	V
PD reverse voltage	$V_{R(PD)}$	30	V
Operating temperature	T_{opr}	-10 to +60	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +85	$^\circ\text{C}$

Electrical Characteristics

($T_C = 25^\circ\text{C}$)

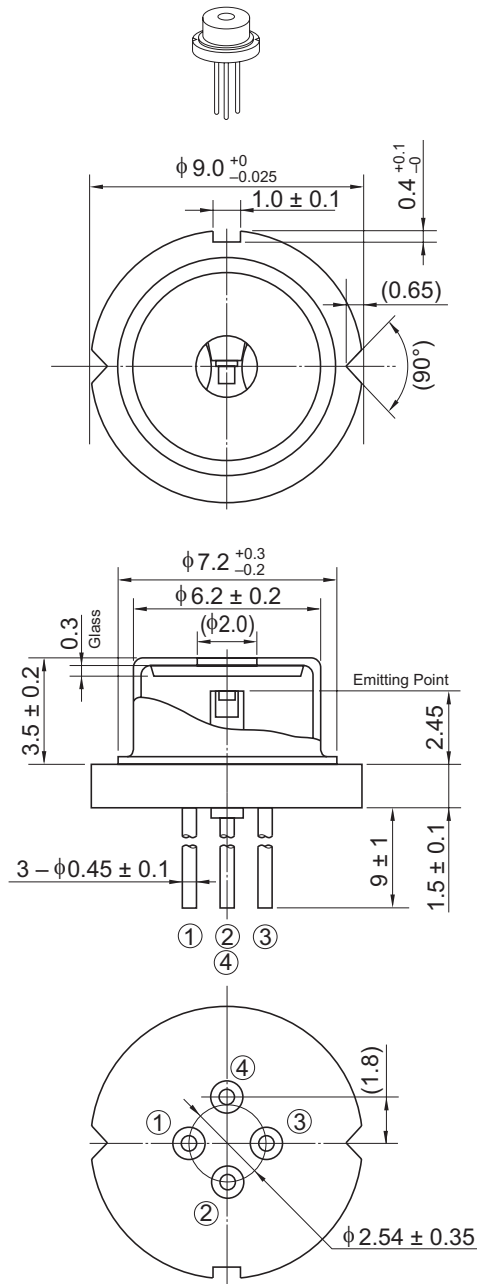
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Threshold current	I_{th}	—	55	70	mA	—
Operating current	I_{OP}	—	140	180	mA	$P_O = 90 \text{ mW}$
Operating voltage	V_{OP}	—	2.4	2.8	V	$P_O = 90 \text{ mW}$
Lasing wavelength	λ_p	654	660	665	nm	$P_O = 90 \text{ mW}$
Beam divergence parallel to the junction	$\theta_{//}$	7	10	13	$^\circ$	$P_O = 90 \text{ mW}$
Beam divergence perpendicular to the junction	θ_{\perp}	15	17	20	$^\circ$	$P_O = 90 \text{ mW}$
Monitor current	I_s	—	0.6	—	mA	$P_O = 90 \text{ mW},$ $V_{R(RD)} = 5\text{V}$

Typical Characteristic Curves



Package Dimensions

As of June, 2005
Unit: mm



OPJ Code	LD/FG
JEDEC	—
JEITA	—
Mass (reference value)	1.1 g

Cautions

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7. Contact our sales office for any questions regarding this document or OPJ products.

1. The laser light is harmful to human body especially to eye no matter what directly or indirectly. The laser beam shall be observed or adjusted through infrared camera or equivalent.
2. This product contains gallium arsenide (GaAs), which may seriously endanger your health even at very low doses. Please avoid treatment which may create GaAs powder or gas, such as disassembly or performing chemical experiments, when you handle the product.
When disposing of the product, please follow the laws of your country and separate it from other waste such as industrial waste and household garbage.
3. Definition of items shown in this CAS is in accordance with that shown in Opto Device Databook issued by OPJ unless otherwise specified.

Sales Offices



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